

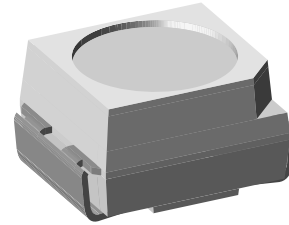
## High Speed Infrared Emitting Diode, 870 nm, GaAIAs Double Hetero

### Description

TSMF3700 is a high speed infrared emitting diode in GaAIAs on GaAIAs double hetero (DH) technology in a miniature PL-CC-2 SMD package.

It has been designed to meet the increasing demand on optoelectronic devices for surface mounting.

The package consists of a lead frame which is surrounded with a white thermoplast. The reflector inside the package is filled up with clear epoxy.



94 8553

### Features

- SMT IRED with extra high radiant power
- Low forward voltage
- Compatible with automatic placement equipment
- EIA and ICE standard package
- Suitable for infrared, vapor phase and wavesolder process
- Available in 8 mm tape
- Suitable for pulse current operation
- Extra wide angle of half intensity  $\varphi = \pm 60^\circ$
- Peak wavelength  $\lambda_p = 870 \text{ nm}$
- High reliability
- Lead-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

### Applications

- Infrared source in tactile keyboards
- IR diode in low space applications
- High performance PCB mounted infrared sensors
- High power infrared emitter for miniature light barriers

### Absolute Maximum Ratings

$T_{amb} = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Reverse Voltage		$V_R$	5	V
Forward current		$I_F$	100	mA
Peak Forward Current	$t_p/T = 0.5, t_p = 100 \mu\text{s}$	$I_{FM}$	200	mA
Surge Forward Current	$t_p = 100 \mu\text{s}$	$I_{FSM}$	1	A
Power Dissipation		$P_V$	160	mW
Junction Temperature		$T_j$	100	$^\circ\text{C}$
Operating Temperature Range		$T_{amb}$	- 55 to + 100	$^\circ\text{C}$
Storage Temperature Range		$T_{stg}$	- 55 to + 100	$^\circ\text{C}$
Soldering Temperature	$t \leq 10 \text{ sec}$	$T_{sd}$	260	$^\circ\text{C}$
Thermal Resistance Junction/Ambient		$R_{thJA}$	450	K/W

### Electrical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Forward Voltage	$I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$	$V_F$		1.4	1.7	V
	$I_F = 1\text{ A}$ , $t_p = 100\text{ }\mu\text{s}$	$V_F$		2.4		V
Temp. Coefficient of $V_F$	$I_F = 100\text{ mA}$	$TK_{V_F}$		-1.7		mV/K
Reverse Current	$V_R = 5\text{ V}$	$I_R$			10	$\mu\text{A}$
Junction capacitance	$V_R = 0\text{ V}$ , $f = 1\text{ MHz}$ , $E = 0$	$C_j$		160		pF

### Optical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Radiant Intensity	$I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$	$I_e$	5	7	25	mW/sr
	$I_F = 1\text{ A}$ , $t_p = 100\text{ }\mu\text{s}$	$I_e$		60		mW/sr
Radiant Power	$I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$	$\phi_e$		32		mW
Temp. Coefficient of $\phi_e$	$I_F = 100\text{ mA}$	$TK_{\phi_e}$		-0.8		%/K
Angle of Half Intensity		$\phi$		$\pm 60$		deg
Peak Wavelength	$I_F = 100\text{ mA}$	$\lambda_p$		870		nm
Spectral Bandwidth	$I_F = 100\text{ mA}$	$\Delta\lambda$		40		nm
Temp. Coefficient of $\lambda_p$	$I_F = 100\text{ mA}$	$TK_{\lambda_p}$		0.2		nm/K
Rise Time	$I_F = 100\text{ mA}$	$t_r$		30		ns
Fall Time	$I_F = 100\text{ mA}$	$t_f$		30		ns
Virtual Source Diameter		$\emptyset$		0.5		mm

### Typical Characteristics ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

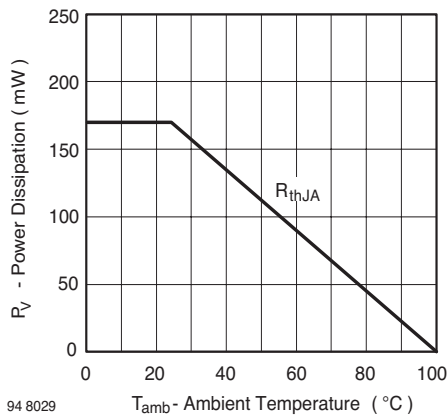


Figure 1. Power Dissipation vs. Ambient Temperature

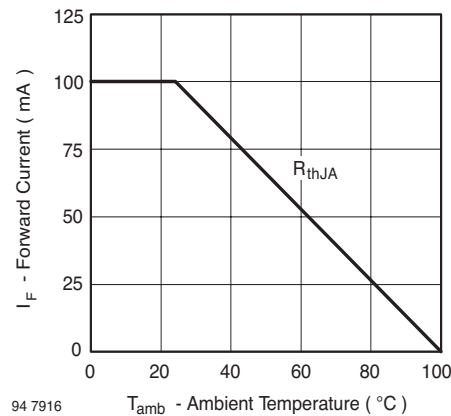


Figure 2. Forward Current vs. Ambient Temperature

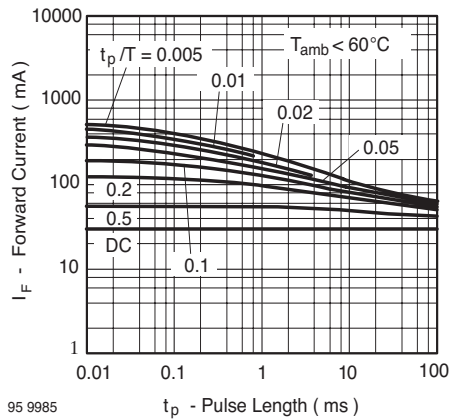


Figure 3. Pulse Forward Current vs. Pulse Duration

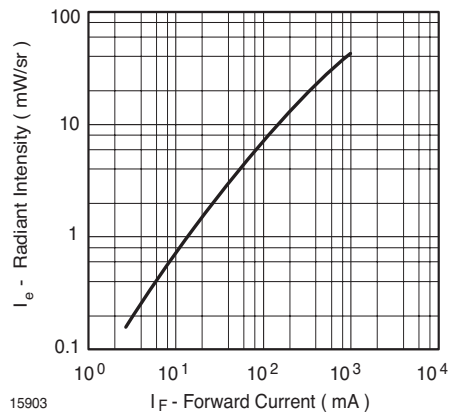


Figure 6. Radiant Intensity vs. Forward Current

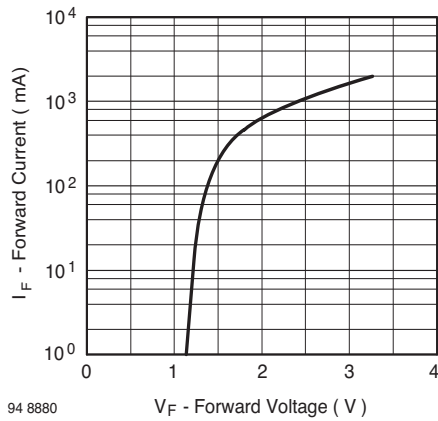


Figure 4. Forward Current vs. Forward Voltage

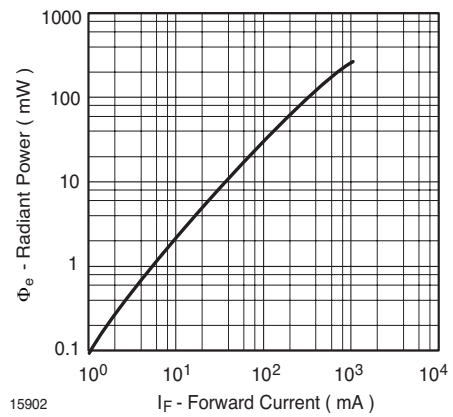


Figure 7. Radiant Power vs. Forward Current

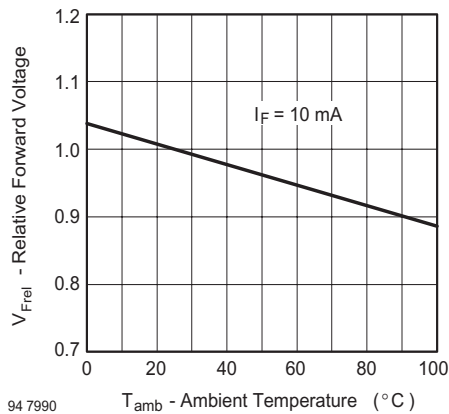


Figure 5. Relative Forward Voltage vs. Ambient Temperature

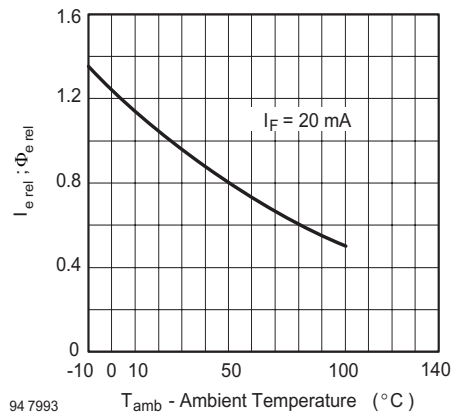


Figure 8. Rel. Radiant Intensity/Power vs. Ambient Temperature

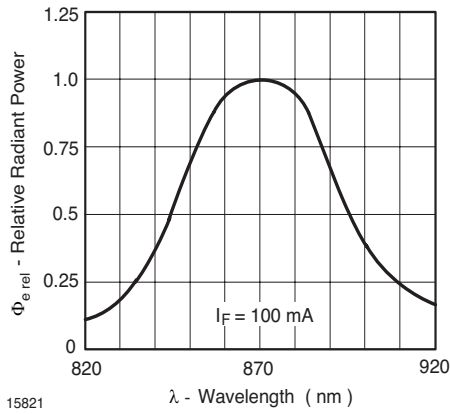


Figure 9. Relative Radiant Power vs. Wavelength

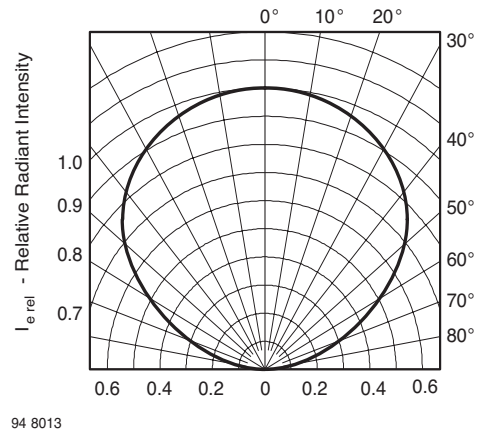
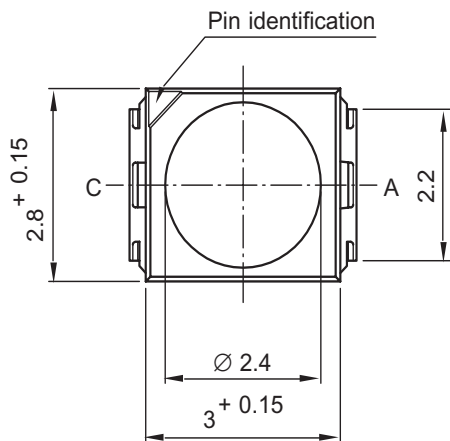
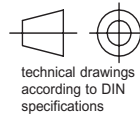
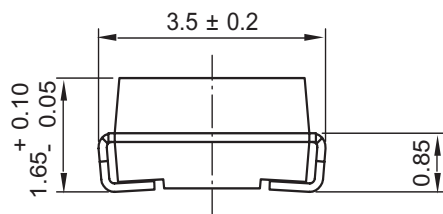
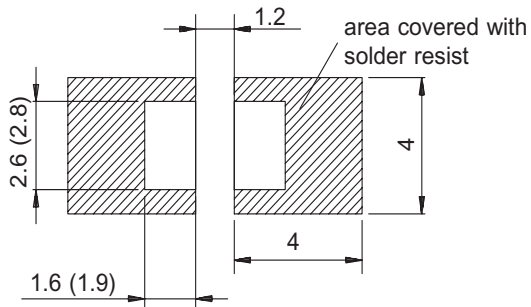


Figure 10. Relative Radiant Intensity vs. Angular Displacement

## Package Dimensions in mm



### Mounting Pad Layout



Dimensions: IR and Vaporphase (Wave Soldering)

Drawing-No. : 6.541-5025.01-4  
Issue: 7; 05.04.04

95 11314



## Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany  
Telephone: 49 (0)7131 67 2831, Fax number: 49 (0)7131 67 2423



### Notice

Specifications of the products displayed herein are subject to change without notice. Vishay Intertechnology, Inc., or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document. Except as provided in Vishay's terms and conditions of sale for such products, Vishay assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of Vishay products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Vishay for any damages resulting from such improper use or sale.